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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

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Kind regards,

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BSS138P

60 V, 360 mA N-channel Trench MOSFET Rev. 1 — 2 November 2010

Product data sheet

Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25 ^{\circ}C$	-	-	60	V
V_{GS}	gate-source voltage	$T_{amb} = 25 ^{\circ}C$	-	-	±20	V
I_D	drain current	$T_{amb} = 25 ^{\circ}C;$ $V_{GS} = 10 ^{\circ}V$	[1] -	-	360	mA
R _{DSon}	drain-source on-state resistance	$T_j = 25 ^{\circ}\text{C};$ $V_{GS} = 10 \text{V};$ $I_D = 300 \text{mA}$	<u>[2]</u> -	0.9	1.6	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



^[2] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.01$.

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2. Pinning information

Table 2. Pinning

	_			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	S	source	3	D
3	D	drain	1 2	G (F)

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
BSS138P	TO-236AB	plastic surface-mounted package; 3 leads	SOT23	

4. Marking

Table 4. Marking codes

Type number	Marking code[1]
BSS138P	AN*

^{[1] * =} placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

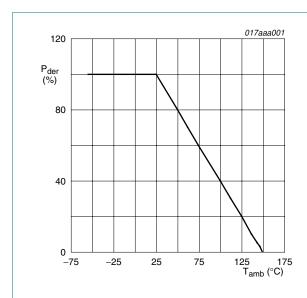
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25 ^{\circ}C$	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	±20	V
I_D	drain current	$V_{GS} = 10 \text{ V}$	<u>[1]</u>		
		T _{amb} = 25 °C	-	360	mA
		T _{amb} = 100 °C	-	230	mA
I _{DM}	peak drain current	$T_{amb} = 25 ^{\circ}C;$ single pulse; $t_p \le 10 \mu s$	-	1.2	Α

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Table 5. Limiting values ...continued In accordance with the Absolute Maximum Rating System (IEC 60134).

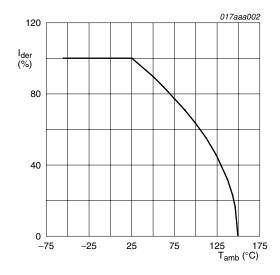
Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot} total power dissipation	•	[2] -	350	mW	
		[1] -	420	mW	
		$T_{sp} = 25 ^{\circ}C$	-	1140	mW
Tj	junction temperature			150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C
Source-d	rain diode				
I _S	source current	T _{amb} = 25 °C	<u>[1]</u> -	360	mA

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$

Fig 1. Normalized total power dissipation as a function of ambient temperature

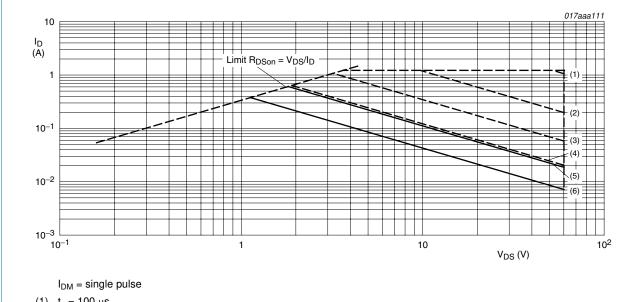


$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

Fig 2. Normalized continuous drain current as a function of ambient temperature

BSS138P NXP Semiconductors

60 V, 360 mA N-channel Trench MOSFET



- (1) $t_p = 100 \mu s$
- (2) $t_p = 1 \text{ ms}$
- (3) $t_p = 10 \text{ ms}$
- (4) $t_p = 100 \text{ ms}$
- (5) DC; $T_{sp} = 25 \, ^{\circ}C$
- (6) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 1 cm²

Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	310	370	K/W
			[2] _	260	300	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	115	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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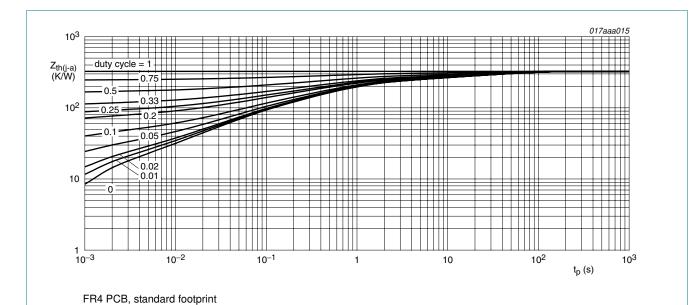
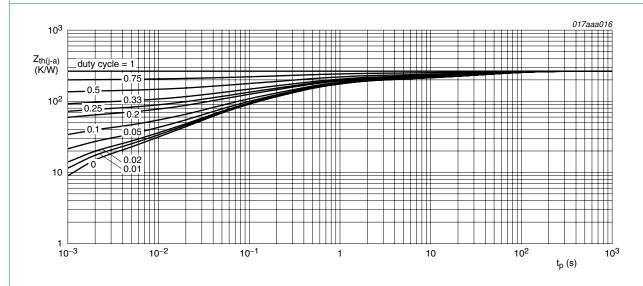


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

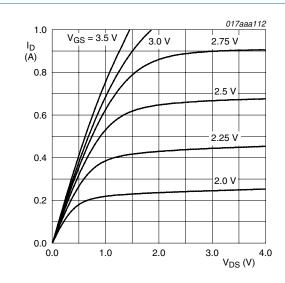
Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D=10~\mu\text{A};V_{GS}=0~V$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}$	0.9	1.2	1.5	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$				
		T _j = 25 °C	-	-	1	μΑ
		T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	100	nA
R _{DSon}	drain-source on-state		[1]			
	resistance	$V_{GS} = 5 \text{ V}; I_D = 50 \text{ mA}$	-	1	2	Ω
		$V_{GS} = 10 \text{ V}; I_D = 300 \text{ mA}$	-	0.9	1.6	Ω
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}$	<u>[1]</u> _	700	-	mS
Dynamic o	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 300 \text{ mA};$	-	0.72	8.0	nC
Q_{GS}	gate-source charge	$V_{DS} = 30 \text{ V};$	-	0.14	-	nC
Q_{GD}	gate-drain charge	$-V_{GS} = 4.5 \text{ V}$	-	0.24	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \ V; \ V_{DS} = 10 \ V;$	-	38	50	pF
Coss	output capacitance	f = 1 MHz	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V};$	-	2	6	ns
t _r	rise time	$R_L = 250 \Omega;$ - $V_{GS} = 10 V;$	-	3	-	ns
$t_{d(off)}$	turn-off delay time	$R_{G} = 6 \Omega$	-	9	20	ns
t _f	fall time		-	4	-	ns
Source-dr	ain diode					
V_{SD}	source-drain voltage	$I_S = 115 \text{ mA}; V_{GS} = 0 \text{ V}$	0.47	0.75	1.1	٧

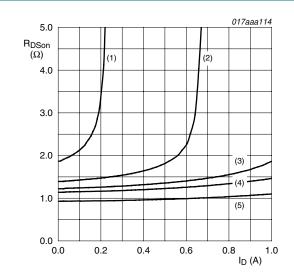
^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.01.$

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 $T_{amb} = 25 \, ^{\circ}C$

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



T_{amb} = 25 °C

(1) $V_{GS} = 2.0 \text{ V}$

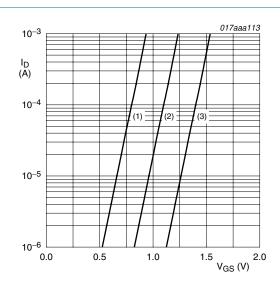
(2) $V_{GS} = 2.5 \text{ V}$

(3) $V_{GS} = 3.0 \text{ V}$

(4) $V_{GS} = 3.5 \text{ V}$

(5) $V_{GS} = 10 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



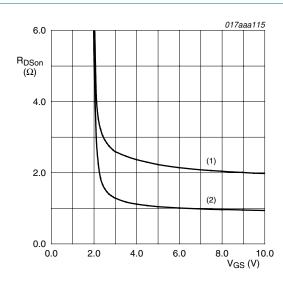
 T_{amb} = 25 °C; V_{DS} = 5 V

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



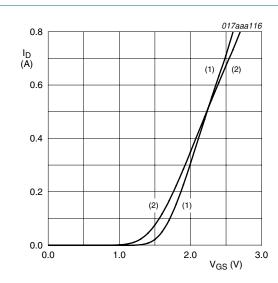
 $I_D = 300 \text{ mA}$

(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

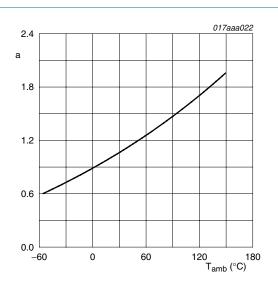
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$$V_{DS} > I_D \times R_{DSon}$$

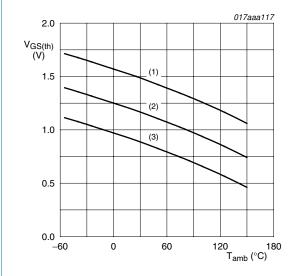
- (1) $T_{amb} = 25 \, ^{\circ}C$
- (2) $T_{amb} = 150 \, ^{\circ}C$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

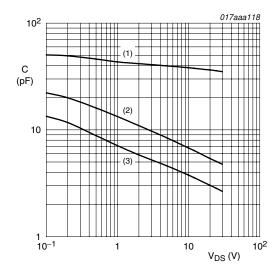
Fig 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of ambient temperature

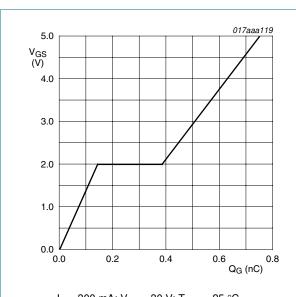


 $f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$

- (1) C_{iss}
- (2) Coss
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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 I_D = 300 mA; V_{DS} = 30 V; T_{amb} = 25 °C

Fig 14. Gate-source voltage as a function of gate charge; typical values

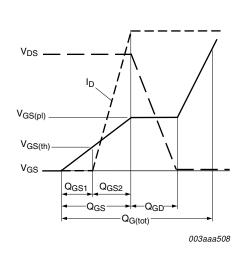
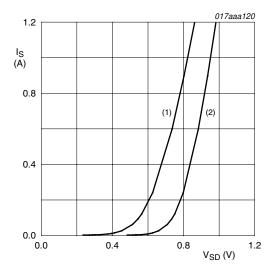


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

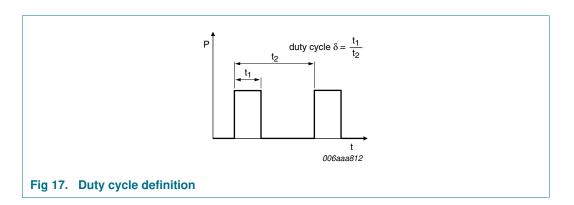
(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

Fig 16. Source current as a function of source-drain voltage; typical values

60 V, 360 mA N-channel Trench MOSFET

8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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9. Package outline

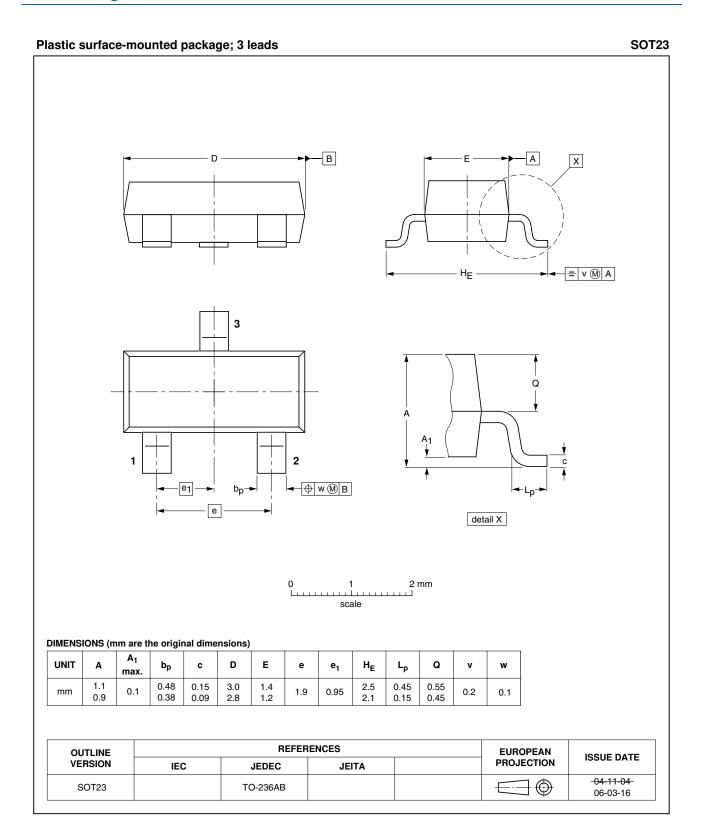
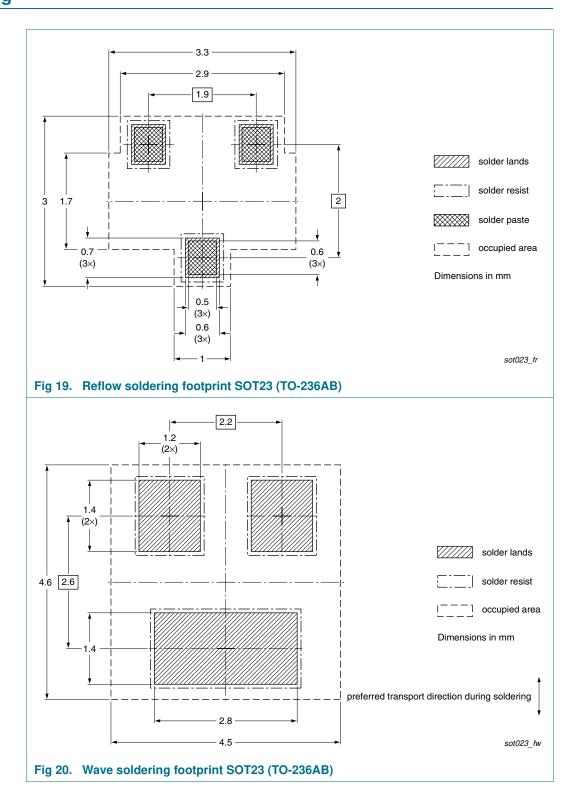


Fig 18. Package outline SOT23 (TO-236AB)

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60 V, 360 mA N-channel Trench MOSFET

10. Soldering



60 V, 360 mA N-channel Trench MOSFET

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BSS138P v.1	20101102	Product data sheet	-	-

60 V, 360 mA N-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BSS138P NXP Semiconductors

60 V, 360 mA N-channel Trench MOSFET

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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60 V, 360 mA N-channel Trench MOSFET

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